

PHASE RELATIONS IN THE AgI-Ag₇GeSe₅I-GeSe₂ SYSTEM

Nurten Bayramova¹, Ilaha Huseynova², Elvira Melikova² & Samira Imamaliyeva²

¹Nakhchivan State University, Nakhchivan, Azerbaijan

²Institute of Catalysis and Inorganic Chemistry, Baku, Azerbaijan

Received: 03 september 2025

Accepted: 30 october 2025

Published: 31 october 2025

Phase equilibria in the AgI-Ag₇GeSe₅I-GeSe₂ system were studied by differential thermal and X-ray diffraction analysis. T-x phase diagrams of boundary systems, liquidus surface projection and a number of internal vertical sections of the T-x-y diagram were constructed. It was found that all three boundary systems are quasi-binary and form eutectic phase diagrams. The AgI-Ag₇GeSe₅I-GeSe₂ system is a quasi-ternary plane of the corresponding quaternary system and belongs to the type with invariant eutectic crystallizing at 525 °C. The liquidus surface projection consists of 3 regions corresponding to the primary crystallization of the α-phase based on Ag₇GeSe₅I, as well as high-temperature modifications of the AgI and GeSe₂ compounds. The liquidus surfaces of HT-GeSe₂ and the α-phase, which have a higher melting point, occupy very large areas, while the liquidus surface of the HT-AgI phase is located in a small region near the corresponding vertex of the concentration triangle.

Keywords: silver iodide, germanium diselenide, argyrodite, phase equilibria

INTRODUCTION

Silver chalcogenides with p² - elements are valuable functional materials with interesting semiconductor, photoelectric, thermoelectric, etc. properties [1–4]. Among these materials, the argyrodite family compounds occupy a special place. Their physicochemical study began in the 60s of the last century. As is known, the argyrodite family includes compounds with the general formula $A_{(42-n)/m}^{m+}B^{n+}X_6^{2-}$. Here, A^{m+} is usually mono- (Cu⁺, Ag⁺, Li⁺) or divalent (Zn²⁺, Cd²⁺, Hg²⁺) cations, Bⁿ⁺ is Ga³⁺, Si⁴⁺, Ge⁴⁺, Sn⁴⁺, P⁵⁺, As⁵, cations, and X²⁻ is S²⁻, Se²⁻, Te²⁻ anions. These compounds are valuable environmentally safe functional materials that exhibit thermoelectric, photoelectric, and optical properties and have great potential for application in solar converters, as well as in various photovoltaic processes [5-12].

In addition to chalcogenide argyrodites, there are also argyrodites with multiple quaternary anion substitutions of the type $A_7B^{IV}X_5Y$ (Y=Cl, Br, I), in which one of the 6 chalcogen atoms in their formula is replaced by a halogen [5, 9]. Many of these compounds have high ionic conductivity and are promising for use as ion-selective electrodes, solid electrolytes, etc. [9, 13-19].

One of the most effective ways to establish the physicochemical basis for obtaining new multicomponent phases is the study of phase equilibria in the relevant systems [9, 10, 20]. Recent studies have focused on phase equilibria in various systems significant for the exploration of new variable-composition phases within the argyrodite family of compounds [9, 10, 21-29].

The $\text{Ag}_2\text{Se-Agl-GeSe}_2$ solid-state plane of the Ag-Ge-Se-I four-component system is of interest in terms of the search for chalcogen→halogen-substituted phases based on argyrodite compounds. When planning experimental work to study this solid-state plane, it became clear that there is no information about it in the scientific literature.

Taking into account the above, we decided to study phase equilibria in the $\text{Ag}_2\text{Se-Agl-GeSe}_2$ system. The presented work presents the results of the study of this system in the $\text{Agl-Ag}_7\text{GeSe}_5\text{I-GeSe}_2$ solid-state plane.

The initial compounds of the system have been studied in detail. The AgI compound melts congruently at 558 °C and undergoes polymorphic transformation at 147 °C. The high-temperature modification (HT-Agl) crystallizes in a cubic structure (Sp.gr. $Im\bar{3}m$, $a=5.062$ Å), while the low-temperature modification (RT-Agl) crystallizes in a hexagonal (Sp.gr. $P6_3mc$, $a=4.99$ Å, $c=7.520$ Å) structure [30, 31]. HT-Agl is a classic representative of cation-conducting (Ag^+) solid electrolytes. The electrical conductivity of this phase ($\sim 1 \text{ Om}^{-1}\text{cm}^{-1}$) was determined as early as 1914 by K. Tubandt and E. Lorenz [30]. Its anomalously high electrical conductivity is due to the properties of the crystal structure. There are 42 positions for Ag^+ ions in the elementary lattice, and 21 vacant positions fall on each silver cation in one elementary lattice. Silver ions can easily move from one of these positions to another, that is, they are delocalized. This leads to its high ionic conductivity [30-33].

The GeSe_2 compound melts congruently at 742 °C. This compound also has a polymorphic transformation. The low-temperature (25-579°C) modification is rhombic (Sp.gr. $Pmnm$, $a=6.950$, $b=12.220$, $c=23.040$ Å $z=24$), while the high-temperature (579-742°C) modification crystallizes in the monoclinic syngony (Sp.gr. $P2_1/c$, $a=7.030$, $b=16.840$, $c=11.820$ Å, $\alpha = 90^\circ 74'$, $z = 16$) [34, 35].

The compound $\text{Ag}_7\text{GeSe}_5\text{I}$ melts congruently at 870 °C and crystallizes in a cubic structure (Sp.gr. $F\bar{4}3m$, $a=10.72.2(7)$ Å [14], $a=10.986$ Å [36] or $a=11.034$ (5) Å [37], it is a characteristic superionic conductor [13].

EXPERIMENTAL

To study the nature of the physicochemical interaction in the $\text{Agl-Ag}_7\text{GeSe}_5\text{I-GeSe}_2$ system, initial binary compounds (20 grams each) were synthesized. The synthesis was carried out by co-melting mixtures of high-purity simple substances (Ag- rod, 99.997%, CAS 7440-22-4; Ge- ingot, 99.999%, CAS 7440-56-4; Se- granule, 99.999%, CAS 7782-49-2; I- powder, 99.999%, CAS 7553-56-2, AgI-powder) taken in stoichiometric proportions in quartz ampoules under vacuum conditions (10^{-2} Pa).

Since the saturated vapor pressures of iodine ($T_b=184$ °C) and selenium ($T_b=685$ °C [38]) at the melting temperatures of the compounds are high, the synthesis of all three compounds was carried out in a two-zone mode in an inclined furnace.

For the synthesis of AgI, $\text{Ag}_7\text{GeSe}_5\text{I}$, and GeSe_2 compounds, a quartz ampoule with a length of ~ 15 cm and an internal diameter of ~ 1.4 - 1.6 cm, previously cleaned with a chromium mixture, was used. Due to the volatility of elemental iodine, for the synthesis of the first two compounds, the required amount of silver was first weighed and placed in the ampoule, then iodine was added to the ampoule cooled in ice water, and was vacuumed and sealed.

During the synthesis of all three compounds, a part of the ampoule (~ 6 cm) remained outside the furnace. To control the vapor pressure of the volatile element and prevent the ampoule from exploding, the part of the ampoule remaining outside the furnace ("cold" zone) was cooled with water. The furnace was gradually heated to a temperature 30–500 °C higher than the melting point of the synthesized compound ("hot zone"). In the "cold" zone,

the volatile component condensed and returned to the "hot" zone and entered the reaction. During the reaction, the amount of the volatile component gradually decreased and after a while, it was practically completely consumed. After that, the ampoule was completely inserted into the furnace, kept at 580 °C (AgI), 780 °C (GeSe₂), or 900 °C (Ag₇GeSe₅I) for 1 hour, and then slowly cooled.

The individuality of the synthesized samples was confirmed by DTA and XRD methods. Two thermal effects were detected in the DTA heating curves of AgI, GeSe₂ compounds: 147 °C and 558 °C (AgI), 579 and 742 °C (GeSe₂). Small peaks with lower temperatures (147 and 579 °C) correspond to the polymorphic transition temperatures of these compounds, and high-temperature endoeffects (558 and 742 °C) to their melting temperatures. Only one peak (870 °C) was detected on the DTA heating curve of the Ag₇GeSe₅I compound, corresponding to the melting temperature of this compound. These indicators are in full agreement with the literature data [30-37].

X-ray phase analysis also confirmed the homogeneity of the synthesized samples. The powder diffractograms had diffraction patterns known from the literature for low-temperature modifications of both compounds. The crystal lattice parameters calculated on their basis coincide with those given in the literature [30-37].

By melting mixtures of the obtained initial compounds in various proportions in vacuumed quartz ampoules, the AgI-GeSe₂, 0,2Ag₇GeSe₅I-GeSe₂, and 0,2Ag₇GeSe₅I-AgI side systems, as well as alloys with 3 internal sections ([A] – GeSe₂, [B] – AgI and 0.2 Ag₇GeSe₅I- [C], [A], [B], [C] – compositions corresponding to a 1:1 molar ratio of the components on the sides of the concentration triangle) were prepared. To maximally approach the equilibrium state, the samples were gradually cooled to 450 °C and thermally treated at this temperature for 500 hours.

The studies were carried out in closed ampoules by DTA (NETZSCH 404 F1Pegasus system, heating rate 10 deg. / min, chromel-alumel thermocouples) and XRD (Bruker D8 ADVANCE diffractometer, CuK_{α1} radiation, 2θ = 5-75 °). The temperature was determined with an error of ±2°, and the crystal lattice parameters with an error of ±0.00001 Å.

RESULTS AND DISCUSSION

As a result of the combined analysis of the XRD and DTA results of the heat-treated samples, a full scheme of the phase equilibria in the AgI-Ag₇GeSe₅I-GeSe₂ system was obtained. Before the formula of the compound Ag₇GeSe₅I in the concentration triangle and the corresponding sections, the coefficient 0.2 is written so that the expression of the composition in this composition region is the same as in the concentration triangle Ag₂Se-AgI-GeSe₂.

Boundary quasi-binary systems

Powder diffractograms of annealed samples of boundary systems are given in Fig. 1.

As can be seen, the diffraction patterns of the intermediate alloys in all three systems consist of sets of diffraction reflections of the corresponding initial compounds. There are no new diffraction lines in the alloys, the reflection angles of the equilibrium phases are the same as the diffraction lines of the corresponding initial compounds. This indicates that all three boundary systems are stable in the subsolidus, i.e., they consist of 2-phase mixtures of the corresponding initial compounds, and there are no areas of homogeneity that can be felt based on these compounds.

Based on the DTA and XRD data, the phase diagrams of the AgI-GeSe₂, 0,2Ag₇GeSe₅I-GeSe₂, and 0,2Ag₇GeSe₅I-AgI were constructed.

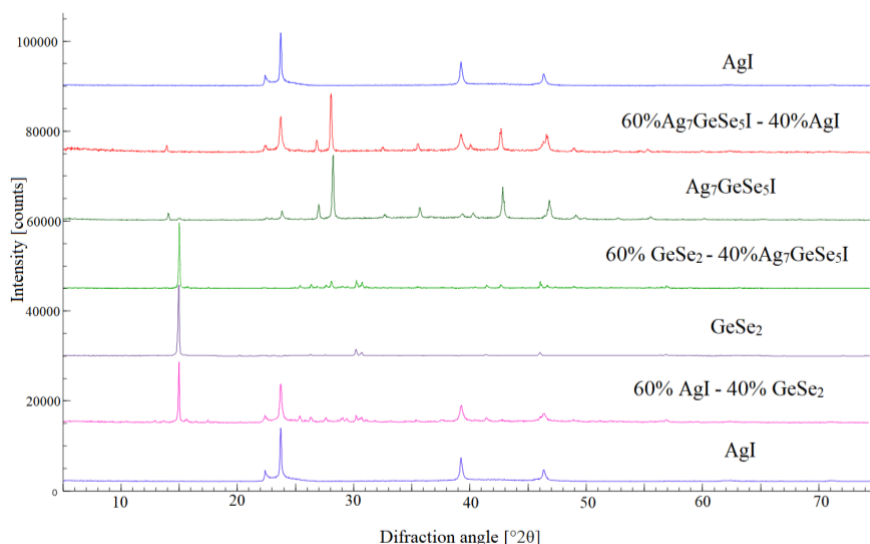


Figure 1. Powder diffractograms of samples of boundary systems

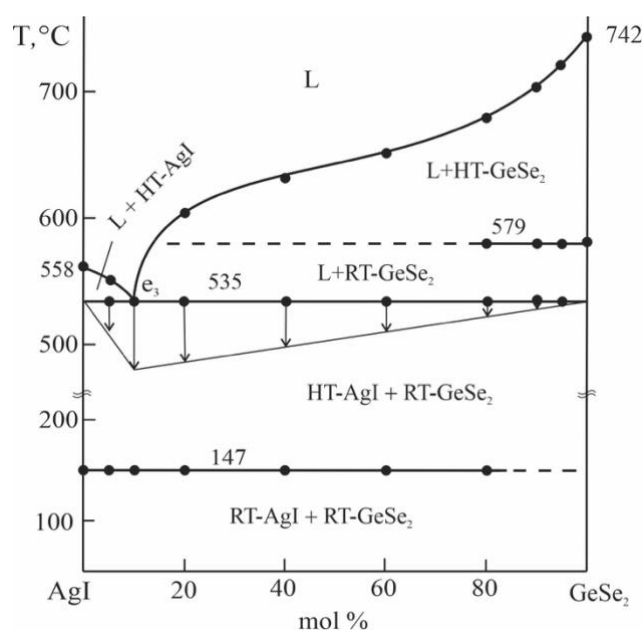


Figure 2. Phase diagram of the AgI-GeSe₂ system

As can be seen from Fig.2, the AgI-GeSe₂ system is quasi-binary and has a eutectic-type phase diagram. The eutectic has a 10 mol % GeSe₂ content and crystallizes at 535 °C.

In the 0,2Ag₇GeSe₅I-AgI system, the eutectic crystallizes at the composition of 92 mol% AgI and 545 °C (Fig.3). At the eutectic temperature, there is a solid solution area of 7-8 mol % based on Ag₇GeSe₅I. The polymorphic transformation temperature of the AgI compound in the system is constant and has the same value as that of pure AgI. This indirectly indicates that the solubility in AgI is very small.

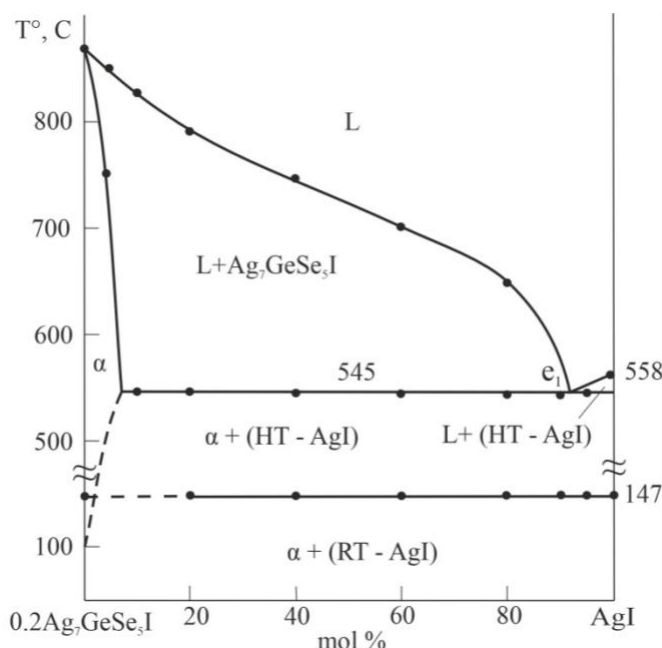


Figure 3. Phase diagram of the 0,2Ag₇GeSe₅I-AgI system

0.2Ag₇GeSe₅I-GeSe₂ system (Fig.4). In this system, the eutectic has coordinates 40 mol % GeSe₂ and 542 °C. The fact that the polymorphic transformation temperature of the GeSe₂ compound remains constant indicates that its solubility is very low.

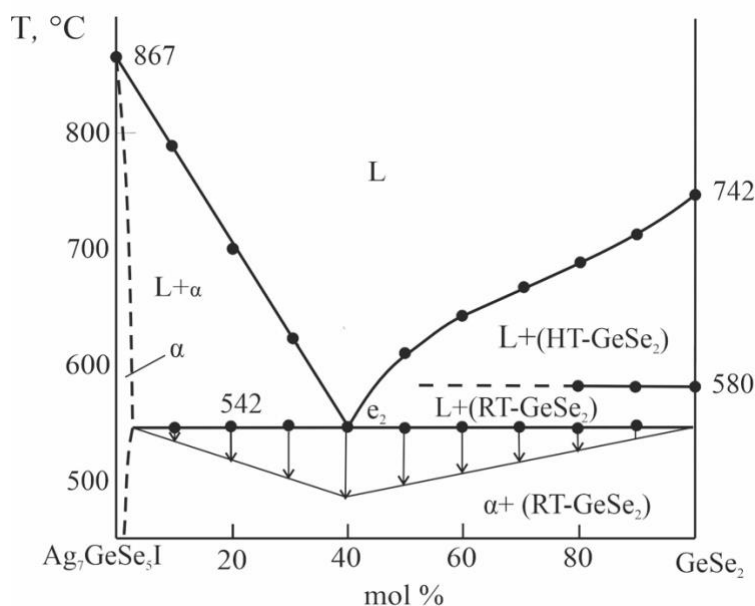


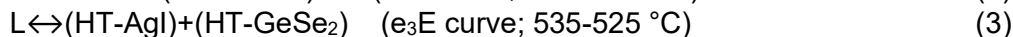
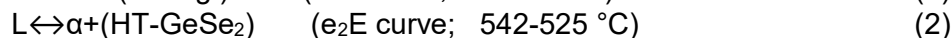
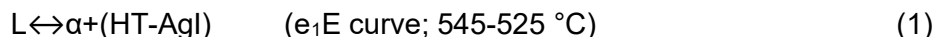
Figure 4. Phase diagram of the 0,2Ag₇GeSe₅I-GeSe₂ system

Liquidus surface of the AgI-Ag₇GeSe₅I-GeSe₂ system

The fact that all three sides of the 0,2Ag₇GeSe₅I- AgI- GeSe₂ concentration triangle are quasi-binary allows it to be characterized as an independent subsystem of the Ag₂Se-AgI-GeSe₂ quasi-ternary system.

Based on the DTA results, a projection of liquidus surface projection of the 0,2Ag₇GeSe₅I- AgI- GeSe₂ system was constructed (Fig. 5). As can be seen, the system belongs to the eutectic type. The liquidus consists of 3 areas corresponding to the initial crystallization of the α -phase based on Ag₇GeSe₅I, as well as high-temperature modifications of the AgI and GeSe₂ compounds. While the liquidus surfaces of the HT-

GeSe₂ and α-phases, which have a higher melting temperature, occupy very large areas, the liquidus surface of the HT-Agl phase is located in a small area near the corresponding vertex of the composition triangle. Liquidus surfaces are bounded by eutectic curves reflecting the following



monovariant equilibria.

Crystallization ends at 525 °C via a nonvariant process



The composition of the crystallizing liquid (E) according to this scheme is approximately 75 mol% AgI and 10 mol% GeSe₂.

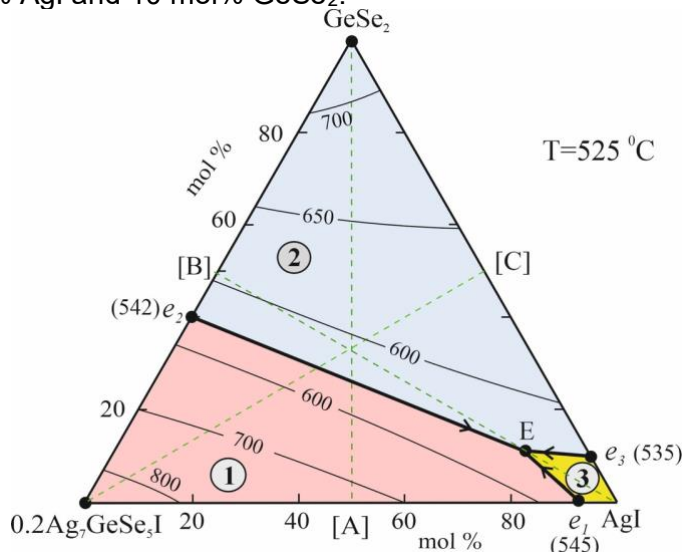


Figure 5. The liquidus surface projection of the 0,2Ag₇GeSe₅I- AgI- GeSe₂ system

Polythermal sections of the phase diagram

To demonstrate the processes of crystallization from the melt, some polythermal sections of the volume phase diagram are constructed: [A] – GeSe₂, [B] – AgI, and 0.2 Ag₇GeSe₅I – [C]. Here [A], [B], and [C] – are the compositions corresponding to the 1:1 molar ratio of the components on the sides of the concentration triangle.

[A]–GeSe₂ section (Fig.6a). This section passes through the initial crystallization areas of the Ag₇GeSe₅I and HT-GeSe₂ phases (RT-GeSe₂ in a very small composition interval). The intersection point of the liquidus curve (~25 mol % GeSe₂) (2) corresponds to the monovariant eutectic equilibrium. This process occurs in all samples with a content of >10 mol % GeSe₂. In the concentration range of 0–10 mol% GeSe₂, after the initial crystallization of the α-phase, a monovariant equilibrium (1) is observed. In all alloys, crystallization ends at 525 °C according to the nonvariant eutectic reaction (4). The horizontal lines at temperatures of 580 and 147 °C reflect polymorphic transformations of the GeSe₂ and AgI compounds.

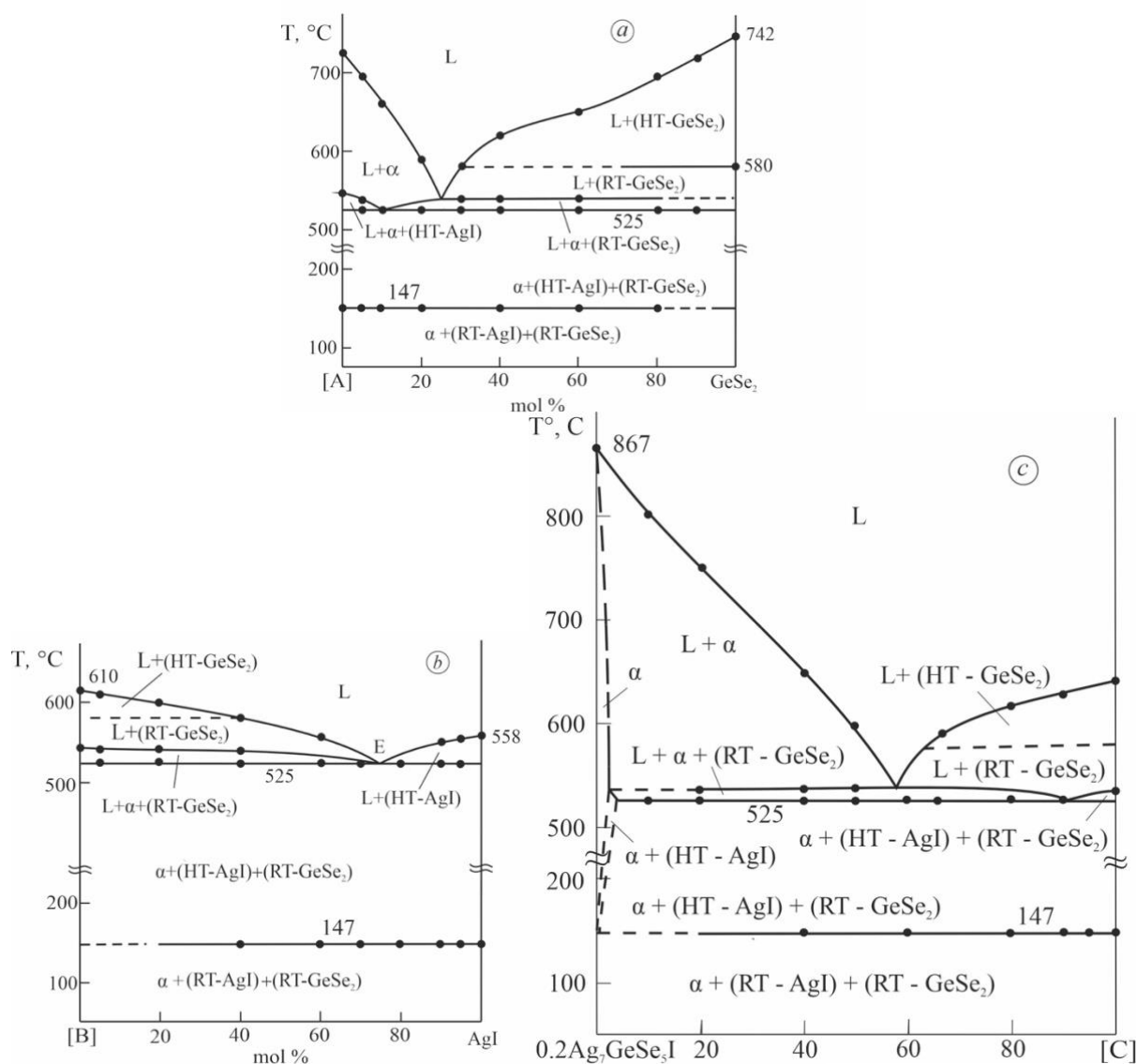


Figure 6. Some polythermal sections of the phase diagram of the $\text{Ag}_2\text{Se-AgI-GeSe}_2$ system

[B]- AgI cross section (Fig. 6b). Comparison of this cross section with the liquidus surface projection (Fig. 3) shows that it passes through the liquidus surfaces of GeSe_2 and AgI compounds and the triple eutectic point (E). Although thermal effects corresponding to the polymorphic transformation of the GeSe_2 compound are not detected in the DTA curves (this may be due to their very small intensity), this transformation is marked by broken lines at 780 $^{\circ}\text{C}$ in Fig. 4b.

After the initial crystallization of the HT-GeSe_2 and RT-GeSe_2 phases from the melt, monovariant eutectic crystallization (2) occurs. This leads to the formation of a three-phase region $L+\alpha+(RT-\text{GeSe}_2)$ on the $T-x$ diagram. A sample with a 75 mol % GeSe_2 content has a eutectic composition (E) and crystallizes invariantly at 525 $^{\circ}\text{C}$. In samples richer in AgI , the (HT-AgI) and then the ternary eutectic crystallizes first.

$0.2 \text{Ag}_7\text{GeSe}_5\text{I} - [\text{C}]$ section (Fig. 6c). In this section, from left to right, the α -phase and 2 modifications of the GeSe_2 compound crystallize. At the intersection of the liquidus curves, monovariant crystallization of the $\alpha+(RT-\text{GeSe}_2)$ eutectic mixture occurs. This process occurs in all samples with a content of >10 mol% $0.2 \text{Ag}_7\text{GeSe}_5\text{I}$. In the 0–10 mol% $0.2 \text{Ag}_7\text{GeSe}_5\text{I}$ content interval, after the initial crystallization of (RT-GeSe_2) , co-crystallization of the $(\text{HT-AgI})+(\text{RT-GeSe}_2)$ eutectic mixture takes place. As in other sections, crystallization is completed by the monovariant eutectic process (4), and at 147 $^{\circ}\text{C}$, the $(\text{HT-AgI}) \rightarrow (\text{RT-AgI})$ polymorph transition occurs in this mixture.

CONCLUSION

Thus, in this work, phase relationships in the quasi-ternary AgI-Ag₇GeSe₅I-GeSe₂ system were studied using physicochemical analysis methods. Phase diagrams of the side systems, projections of the liquidus surface, and a number of the cross sections of the volume diagram were constructed. It was shown that all three side systems are eutectic type quasi-binary systems. In the studied system, the ternary eutectic point crystallizes at 525°C.

The obtained experimental data can be used to select alloy compositions that are of interest as potential environmentally friendly thermoelectric materials with anomalously low thermal conductivity and mixed ionic-electronic conductors.

REFERENCES

- [1] Babanly, M.B.; Yusibov, Yu.A.; Abishev, V.T. Three-component chalcogenides based on copper and silver. Baku: BSU, 1993, 342 p.
- [2] Ahluwalia, G.K. Applications of Chalcogenides. Springer, 2016
- [3] Woodrow, P. Chalcogenides: Advances in Research and Applications. Nova Science Publishers, 2018.
- [4] Scheer, R., Schock, H.W. Chalcogenide Photovoltaics: Physics, Technologies, and Thin Film Devices. Wiley-VCH, 2011, 384 p.
- [5] Kuhs, W.F.; Nitsche, R.; Scheunemann, K. The argyrodites – a new family of tetrahedrally close-packed structures. *Material Research Bulletin*, **1979**, *14*(2), pp. 241-248, [https://doi.org/10.1016/0025-5408\(79\)90125-9](https://doi.org/10.1016/0025-5408(79)90125-9)
- [6] Nilges, T.; Pfitzner, A. A structural differentiation of quaternary copper argyrodites: structure – property relations of high temperature ion conductors. *Zeitschrift für Kristallographie – Crystalline Materials*, **2005**, *220*(2-3), pp. 281-294, <https://doi.org/10.1524/zkri.220.2.281.59142>
- [7] Li, J.; Wu, N. Semiconductor-based photocatalysts and photoelectrochemical cells for solar fuel generation, a review. *Catalysis Science & Technology*, **2015**, *5*, pp. 1360-1384, <https://doi.org/10.1039/C4CY00974F>
- [8] Lin, S.; Li, W.; Pei, Y. Thermally insulative thermoelectric argyrodites. *Materials Today*, **2021**, *48*, pp. 198-213, <https://doi.org/10.1016/j.mattod.2021.01.007>
- [9] Babanly, M.B.; Yusibov, Y.A.; Imamaliyeva, S.Z.; Babanly, D.M.; Alverdiyev, I.J. Phase diagrams in the development of the argyrodite family compounds and solid solutions based on them. *Journal of phase equilibria and diffusion*, **2024**, *45*, pp. 228-255, <https://doi.org/10.1007/s11669-024-01088-w>
- [10] Babanly, M.B.; Mashadiyeva, L.F.; Imamaliyeva, S.Z.; Babanly, D.M.; Tagiev, D.B.; Yusibov, Yu.A. Complex copper-based chalcogenides: a review of phase equilibria and thermodynamic properties. *Condensed Matter and Interphases*, **2024**, *26*(4), pp. 579-619, <https://doi.org/10.17308/kcmf.2024.26/12367>
- [11] Alverdiyev, I.J.; Imamaliyeva, S.Z.; Akhmedov, E.I.; Yusibov, Yu.A.; Babanly, M.B. Thermodynamic properties of some ternary compounds of the argyrodite family, *Azerbaijan Chemical Journal*, **2023**, *4*, pp. 21-30, <https://doi.org/10.32737/0005-2531-2023-4-21-30>
- [12] Wang, B.; Li, S.; Luo, Y.; Yang, J.; Ye, H.; Liu, Y.; Jiang, Q. A new thermoelectric Ag₈SiSe₆ argyrodite for room temperature application: sensitivity of thermoelectric performance to cooling conditions. *Material Advances*, **2024**, *5*, pp.3735, <https://doi.org/10.1039/D3MA01190A>
- [13] Laqibi, M.; Cros, B.; Peytavin, S.; Ribes, M. New silver superionic conductors Ag₇XY₅Z (X = Si, Ge, Sn; Y = S, Se; Z = Cl, Br, I) – Synthesis and electrical

- studies. *Solid State Ion*, **1987**, 23(1-2), pp. 21-26, [https://doi.org/10.1016/0167-2738\(87\)90077-4](https://doi.org/10.1016/0167-2738(87)90077-4)
- [14] Nagel, A.; Range, K.J. Die Kristallstruktur von Ag_7GeS_5 . *Zeitschrift für Naturforschung B*, **1979**, 34, pp. 360-362.
- [15] Studenyak, I.P.; Kranjčec, M.; Kovacs, Gy.Sh.; Desnica-Frankovic, I.D.; Molnar, A.A.; Panko, V.V.; Slivka, V.Yu. Electrical and optical absorption studies of Cu_7GeS_5 fast-ion conductor. *Journal of Physics and Chemistry of Solids*, **2002**, 63(2), pp. 267-271, [https://doi.org/10.1016/S0022-3697\(01\)00139-1](https://doi.org/10.1016/S0022-3697(01)00139-1)
- [16] Pogodin, A.I.; Filep, M.; Malakhovska, T.; Vakulchak, V.; Komanicky, V. Recrystallization effect on mechanical parameters and increasing of Ag^+ ionic conductivity in $\text{Ag}_7(\text{Si}_{1-x}\text{Ge}_x)\text{S}_5$ ceramic materials. *Solid State Science*, **2023**, 140, pp. 107203, <https://doi.org/10.1016/j.solidstatesciences.2023.107203>
- [17] Studenyak, I.P.; Pogodin, A.I.; Studenyak, V.I.; Filep, M.J.; Kokhan, O.P.; Kúš, P.; Azhniuk, Y.M.; Zahn, D.R.T. Structure, electrical conductivity, and Raman spectra of $(\text{Cu}_{1-x}\text{Ag}_x)_7\text{GeS}_5$ and $(\text{Cu}_{1-x}\text{Ag}_x)_7\text{GeSe}_5$ mixed crystals. *Material Research Bulletin*, **2021**, 135, pp. 111116, <https://doi.org/10.1016/j.materresbull.2020.111116>
- [18] Studenyak, I.P.; Kranjec, M.; Bilanchuk, V.V.; Kokhan, O.P.; Orliukas, A.F.; Kazakevicius, E.; Kezionis, A.; Salkus, T. Temperature variation of electrical conductivity and absorption edge in Cu_7GeSe_5 advanced superionic conductor, *Journal of Physics and Chemistry of Solids*, **2009**, 70, pp. 1478-1481, <https://doi.org/10.1016/j.jpcs.2009.09.003>
- [19] Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M. Ion dynamics in the argyrodite compound Ag_7GeSe_5 : non-Arrhenius behavior and complete conductivity spectra. *Solid State Ion*, **2001**, 143(3-4), pp. 445-455, [https://doi.org/10.1016/S0167-2738\(01\)00883-9](https://doi.org/10.1016/S0167-2738(01)00883-9)
- [20] Cantor, B. Exploring Multicomponent Phase Space to Discover New Materials. *Journal of phase equilibria and diffusion*, **2024**, 45, pp. 188–218, <https://doi.org/10.1007/s11669-024-01131-w>
- [21] Bayramova, U.R.; Babanly, K.N.; Ahmadov, E.I.; Mashadiyeva, L.F.; Babanly, M.B. Phase equilibria in the $\text{Cu}_2\text{S-Cu}_8\text{SiS}_6\text{-Cu}_8\text{GeS}_6$ system and thermodynamic functions of phase transitions of the $\text{Cu}_8\text{Si}_{(1-x)}\text{Ge}_x\text{S}_6$ argyrodite phases. *Journal of phase equilibria and diffusion*, **2023**, 44, pp. 509-519. <https://doi.org/10.1007/s11669-023-01054-y>
- [22] Amiraslanova, A.J.; Mammadova, A.T.; Imamaliyeva, S.Z.; Alverdiyev, I.J.; Yusibov, Yu.A.; Babanly, M.B. The $6\text{Ag}_2\text{Se}+\text{Ag}_8\text{GeTe}_6\leftrightarrow 6\text{Ag}_2\text{Te}+\text{Ag}_8\text{GeSe}$ reciprocal system. *Russian Journal of Inorganic Chemistry*, **2023**, 68(8), pp.1054-1064. <https://doi.org/10.1134/S0036023623601046>
- [23] Байрамова, У.Р.; Бабанлы, К.Н.; Машадијева, Л.Ф.; Юсиров, Ю.А.; Бабанлы, М. Б. Фазовые равновесия в системе $\text{Cu}_2\text{Se-Cu}_8\text{SiSe}_6\text{-Cu}_8\text{GeSe}_6$. *Russian Journal of Inorganic Chemistry*, 2023, 11, pp. 345-354, <https://doi.org/10.17223/24135542/15/3>
- [24] Ashirov, G.M.; Babanly, K.N.; Mashadiyeva, L.F.; Yusibov, Yu.A.; Babanly, M.B. Phase equilibria in the $\text{Ag}_2\text{S-Ag}_8\text{GeS}_6\text{-Ag}_8\text{SiS}_6$. *Condensed Matter and Interphases*, **2023**, 25(2), pp. 292-301, <https://doi.org/10.17308/kcmf.2023.25/11168>
- [25] Amiraslanova, A.J.; Mammadova, A.T.; Alverdiyev, I.J.; Yusibov, Yu.A.; Babanly, M.B. $\text{Ag}_8\text{GeS}_6(\text{Se}_6)\text{-Ag}_8\text{GeTe}_6$ Systems: phase relations, synthesis, and characterization of solid solutions. *Azerbaijan Chemical Journal*, **2023**, 1, pp. 22-29, <https://doi.org/10.32737/0005-2531-2023-1-22-29>
- [26] Amiraslanova, A.J.; Babanly, K.N.; Imamaliyeva, S.Z.; Alverdiyev, I.J.; Yusibov, Yu.A.; Babanly M.B. Phase relations in the $6\text{Ag}_2\text{Se}+\text{Ag}_8\text{SiTe}_6\leftrightarrow 6\text{Ag}_2\text{Te}+\text{Ag}_8\text{SiSe}_6$ reciprocal system. *Azerbaijan Chemical Journal*, **2023**, 3, pp. 6-17, <https://doi.org/10.32737/0005-2531-2023-3-6-17>
- [27] Ashirov, G.M.; Babanly, K.N.; Mashadiyeva, L.F.; Yusibov, Y.A.; Babanly, M.B. Phase equilibria in the $\text{Ag}_2\text{Se-Ag}_8\text{GeSe}_6\text{-Ag}_8\text{SiSe}_6$ system and characterization of the $\text{Ag}_8\text{Si}_{1-x}\text{Ge}_x\text{Se}_6$ solid solutions. *Chemical Problems*, **2023**, 3, pp. 229-241, <https://doi.org/10.32737/2221-8688-2023-3-229-241>
- [28] Aslanlı, S.R., Alverdiyev, I.J.; Imamaliyeva, S.Z.; Jafarov, Y.I.; Yusibov, Y.A.; Babanly, M.B. Phase Relations in the $\text{Ag}_2\text{S-Ag}_8\text{SiS}_6\text{-Ag}_8\text{SnS}_6$ System and

- Thermodynamic Properties of Polymorphic Transitions of Argyrodite Phases. *International Journal of Thermophysics*, **2025**, 46, pp. 26 <https://doi.org/10.1007/s10765-025-03501-z>
- [29] Aslanli, S.R.; Babanly, K.N.; Imamaliyeva, S.Z.; Yusibov, Yu.A.; Babanly, M.B. System $\text{Ag}_2\text{Se}-\text{Ag}_8\text{SiSe}_6-\text{Ag}_8\text{SnSe}_6$. *Russian Chemical Bulletin*, **2025**, 74(5)
- [30] Ivanov-Shchits, A.K.; Murin, I.V. *Solid State Ionics. v.1. St. Petersburg: St. Petersburg University, 2000, 616 p.*
- [31] Hull, S. *Superionics: crystal structures and conduction processes. Reports on Progress in Physics*, **2007**, 67 (7), pp. 1233–1314, <https://doi.org/10.1088/0034-4885/67/7/r05>
- [32] Mohan, D.B.; Sunandana, C. Nanophases in mechanochemically synthesized AgI–CuI system: structure, phase stability and phase transitions. *Journal of Physics and Chemistry of Solids*, **2004**, 65(10), pp. 1669–1677, <https://doi.org/10.1016/j.jpcs.2004.04.007>
- [33] Binner, J.G.P.; Dimitrakis, G.; Price, D.M.; Reading, M.; Vaidhyanathan, B. Hysteresis in the α - β phase transition in silver iodide. *Journal of Thermal Analysis and Calorimetry*, **2006**, 84(2), pp. 409–412, <https://doi.org/10.1007/s10973-005-7154-1>
- [34] Vassilev, V.; Tomova, K.; Parvanova, V. Phase equilibria in the GeSe_2 – SnSe system. *Journal of Thermal Analysis and Calorimetry*, **2006**, 86, pp. 199–203, <https://doi.org/10.1007/s10973-006-7500-y>
- [35] Shelimova, L.E.; Tomashik, V.N.; Grytsiv, V.I. *State diagrams in semiconductor materials science. Moscow: Nauka, 1991, 368 p.*
- [36] Albert, S.; Pillet, S.; Lecomte, C.; Pradela A.; Ribesa, M. Disorder in $\text{Ag}_7\text{GeSe}_5\text{I}$, a superionic conductor: temperature-dependent anharmonic structural study. *Acta Crystallographica Section B*, 2008, B64, pp. 1–11, <https://doi.org/10.1107/S0108768107059642>
- [37] Zerouale, A.; Cros, B.; Deroide, B.; Ribes, M. Electrical properties of $\text{Ag}_7\text{GeSe}_5\text{I}$. *Solid State Ionics*, **1988**, pp. 28–30, [https://doi.org/10.1016/0167-2738\(88\)90378-5](https://doi.org/10.1016/0167-2738(88)90378-5)
- [38] Emsley, J. *The Elements*, second edition. London: Clarendon press, 1993, 256 p.